

U.S. Patent Application No. 10/769,146
Attorney Docket No. 351991-991320 (Formerly 2102475-991320)

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Cancelled).

Claim 2 (Currently Amended): The semiconductor integrated circuit according to Claim ~~2230~~, wherein each of the first and second the fuse elements has a resistance value that satisfies:

$$V_{OX} > (R_m + R_x) \times I_{esd}$$

where V_{OX} represents a breakdown voltage of a gate oxide films of the MOS transistors, R_m represents a wire resistance value in the electrostatic discharge current path, R_x represents ~~thea~~ total resistance value of the first and second fuse elements, and I_{esd} represents a value of an electrostatic discharge current.

Claim 3 (Currently Amended): The semiconductor integrated circuit according to Claim ~~2129~~, wherein the fuse elements remain[[s]] firm even when energy of 200μJ is applied thereto.

Claim 4 (Currently Amended): The semiconductor integrated circuit according to Claim ~~2129~~, wherein the fuse elements remain[[s]] firm even when energy of 200μJ is applied thereto but breaks when a direct current of 30mA is applied thereto within 20 seconds.

Claim 5 (Currently Amended): The semiconductor integrated circuit according to Claim ~~2129~~, wherein the fuse elements isare electrically disconnected when the semiconductor integrated circuit is mounted on a circuit board.

Claims 6-28 (Cancelled).

Claim 29 (New): A semiconductor integrated circuit, comprising:
an internal circuit;
first and second external terminals connected to the internal circuit;

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first and second fuse elements each having first and second terminals, the first terminals of the first and second fuse elements being connected to the first and second external terminals, respectively; and

a discharge line directly connected to the second terminals of the first and second fuse elements, and serving as an electrostatic discharge current path.

Claim 30 (New): The semiconductor integrated circuit according to claim 29, wherein:
the internal circuit includes a plurality of MOS (Metal Oxide Semiconductor) transistors;
and
the first and second external terminals are connected to gates of the MOS transistors.